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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicants: K. SHIMOHIGASHI et al.  
Serial No.: 08/448,138  
Filed: May 23, 1995  
For: SEMICONDUCTOR MEMORY  
Group: 2511  
Examiner: T. Fears  
Batch No.: P55 - Allowed Files

AMENDMENT UNDER 37 CFR 1.312

Honorable Commissioner of  
Patents and Trademarks  
Washington, D.C. 20231

December 21, 1995

Sir:

In accordance with the provisions of 37 CFR 1.312, please  
further amend the above-identified application as follows:

IN THE CLAIMS

Please add the following new claim:

B1  
6  
-- ~~25~~. A semiconductor memory according to claim ~~24~~,  
further comprising:

a fifth switching MOS transistor having a source-  
drain path provided between one of said pair of data lines and  
a terminal being supplied with said intermediate level  
potential; and

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